



**Vorläufige Daten  
Preliminary Data**

**IGBT, Wechselrichter / IGBT, Inverter  
Höchstzulässige Werte / Maximum Rated Values**

Kollektor-Emitter-Sperrspannung Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = -25^{\circ}\text{C}$	$V_{CES}$	3300 3300	V
Kollektor-Dauergleichstrom Continuous DC collector current	$T_C = 80^{\circ}\text{C}, T_{vj\text{max}} = 150^{\circ}\text{C}$ $T_C = 25^{\circ}\text{C}, T_{vj\text{max}} = 150^{\circ}\text{C}$	$I_{C\text{nom}}$ $I_C$	400 660	A A
Periodischer Kollektor-Spitzenstrom Repetitive peak collector current	$t_P = 1\text{ ms}$	$I_{CRM}$	800	A
Gesamt-Verlustleistung Total power dissipation	$T_C = 25^{\circ}\text{C}, T_{vj\text{max}} = 150$	$P_{tot}$	4,80	kW
Gate-Emitter-Spitzenspannung Gate-emitter peak voltage		$V_{GES}$	+/-20	V

**Charakteristische Werte / Characteristic Values**

			min.	typ.	max.		
Kollektor-Emitter-Sättigungsspannung Collector-emitter saturation voltage	$I_C = 400\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 400\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$V_{CE\text{sat}}$	3,40 4,30	4,25 5,00	V V	
Gate-Schwellenspannung Gate threshold voltage	$I_C = 40,0\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		$V_{G\text{Eth}}$	4,2	5,1	6,0	V
Gateladung Gate charge	$V_{GE} = -15\text{ V} \dots +15\text{ V}, V_{CE} = 1800\text{ V}$		$Q_G$	8,00			$\mu\text{C}$
Interner Gatewiderstand Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		$R_{G\text{int}}$	1,3			$\Omega$
Eingangskapazität Input capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		$C_{ies}$	50,0			nF
Rückwirkungskapazität Reverse transfer capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		$C_{res}$	2,70			nF
Kollektor-Emitter-Reststrom Collector-emitter cut-off current	$V_{CE} = 3300\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$		$I_{CES}$		5,0		mA
Gate-Emitter-Reststrom Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		$I_{GES}$		400		nA
Einschaltverzögerungszeit, induktive Last Turn-on delay time, inductive load	$I_C = 400\text{ A}, V_{CE} = 1800\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{G\text{on}} = 2,7\ \Omega, C_{GE} = 68,0\text{ nF}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$t_{d\text{on}}$	0,28 0,28			$\mu\text{s}$ $\mu\text{s}$
Anstiegszeit, induktive Last Rise time, inductive load	$I_C = 400\text{ A}, V_{CE} = 1800\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{G\text{on}} = 2,7\ \Omega, C_{GE} = 68,0\text{ nF}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$t_r$	0,18 0,20			$\mu\text{s}$ $\mu\text{s}$
Abschaltverzögerungszeit, induktive Last Turn-off delay time, inductive load	$I_C = 400\text{ A}, V_{CE} = 1800\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{G\text{off}} = 3,6\ \Omega, C_{GE} = 68,0\text{ nF}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$t_{d\text{off}}$	1,55 1,70			$\mu\text{s}$ $\mu\text{s}$
Fallzeit, induktive Last Fall time, inductive load	$I_C = 400\text{ A}, V_{CE} = 1800\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{G\text{off}} = 3,6\ \Omega, C_{GE} = 68,0\text{ nF}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$t_f$	0,20 0,20			$\mu\text{s}$ $\mu\text{s}$
Einschaltverlustenergie pro Puls Turn-on energy loss per pulse	$I_C = 400\text{ A}, V_{CE} = 1800\text{ V}, L_S = 60\text{ nH}$ $V_{GE} = \pm 15\text{ V}$ $R_{G\text{on}} = 2,7\ \Omega, C_{GE} = 68,0\text{ nF}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$E_{on}$	470 730			mJ mJ
Abschaltverlustenergie pro Puls Turn-off energy loss per pulse	$I_C = 400\text{ A}, V_{CE} = 1800\text{ V}, L_S = 60\text{ nH}$ $V_{GE} = \pm 15\text{ V}$ $R_{G\text{off}} = 3,6\ \Omega, C_{GE} = 68,0\text{ nF}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$E_{off}$	430 510			mJ mJ
Kurzschlußverhalten SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 2500\text{ V}$ $V_{CE\text{max}} = V_{CES} - L_{S\text{CE}} \cdot di/dt$	$t_P \leq 10\ \mu\text{s}, T_{vj} = 125^{\circ}\text{C}$	$I_{SC}$	2000			A
Wärmewiderstand, Chip bis Gehäuse Thermal resistance, junction to case	pro IGBT / per IGBT		$R_{th\text{JC}}$		26,0		K/kW
Wärmewiderstand, Gehäuse bis Kühlkörper Thermal resistance, case to heatsink	pro IGBT / per IGBT $\lambda_{\text{Paste}} = 1\text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{\text{grease}} = 1\text{ W}/(\text{m}\cdot\text{K})$		$R_{th\text{CH}}$	18,0			K/kW
Temperatur im Schaltbetrieb Temperature under switching conditions			$T_{vj\text{op}}$	-40	125		$^{\circ}\text{C}$

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Vorläufige Daten  
Preliminary Data

## Diode, Wechselrichter / Diode, Inverter

## Höchstzulässige Werte / Maximum Rated Values

Periodische Spitzensperrspannung Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = -25^{\circ}\text{C}$	$V_{RRM}$	3300 3300	V
Dauergleichstrom Continuous DC forward current		$I_F$	400	A
Periodischer Spitzenstrom Repetitive peak forward current	$t_P = 1 \text{ ms}$	$I_{FRM}$	800	A
Grenzlastintegral $I^2t$ - value	$V_R = 0 \text{ V}$ , $t_P = 10 \text{ ms}$ , $T_{vj} = 125^{\circ}\text{C}$	$I^2t$	55,5	$\text{kA}^2\text{s}$
Spitzenverlustleistung Maximum power dissipation	$T_{vj} = 125^{\circ}\text{C}$	$P_{RQM}$	800	kW
Mindesteinschaltdauer Minimum turn-on time		$t_{on \text{ min}}$	10,0	$\mu\text{s}$

## Charakteristische Werte / Characteristic Values

			min.	typ.	max.	
Durchlassspannung Forward voltage	$I_F = 400 \text{ A}$ , $V_{GE} = 0 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$	$V_F$	2,80	3,50	V
	$I_F = 400 \text{ A}$ , $V_{GE} = 0 \text{ V}$	$T_{vj} = 125^{\circ}\text{C}$				
Rückstromspitze Peak reverse recovery current	$I_F = 400 \text{ A}$ , $-di_F/dt = 2200 \text{ A}/\mu\text{s}$ ( $T_{vj}=125^{\circ}\text{C}$ ) $V_R = 1800 \text{ V}$ $V_{GE} = -15 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$	$I_{RM}$	550	650	A A
		$T_{vj} = 125^{\circ}\text{C}$				
Sperrverzögerungsladung Recovered charge	$I_F = 400 \text{ A}$ , $-di_F/dt = 2200 \text{ A}/\mu\text{s}$ ( $T_{vj}=125^{\circ}\text{C}$ ) $V_R = 1800 \text{ V}$ $V_{GE} = -15 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$	$Q_r$	235	440	$\mu\text{C}$ $\mu\text{C}$
		$T_{vj} = 125^{\circ}\text{C}$				
Abschaltenergie pro Puls Reverse recovery energy	$I_F = 400 \text{ A}$ , $-di_F/dt = 2200 \text{ A}/\mu\text{s}$ ( $T_{vj}=125^{\circ}\text{C}$ ) $V_R = 1800 \text{ V}$ $V_{GE} = -15 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$	$E_{rec}$	245	515	mJ mJ
		$T_{vj} = 125^{\circ}\text{C}$				
Wärmewiderstand, Chip bis Gehäuse Thermal resistance, junction to case	pro Diode / per diode		$R_{thJC}$		51,0	K/kW
Wärmewiderstand, Gehäuse bis Kühlkörper Thermal resistance, case to heatsink	pro Diode / per diode $\lambda_{\text{Paste}} = 1 \text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{\text{grease}} = 1 \text{ W}/(\text{m}\cdot\text{K})$		$R_{thCH}$	36,0		K/kW
Temperatur im Schaltbetrieb Temperature under switching conditions			$T_{vj \text{ op}}$	-40	125	$^{\circ}\text{C}$

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